



Inventor: Takehiro Fujii
Title: Side-Emission Type Semiconductor Light-
emitting Device and Manufacturing Method Thereof
Docket: 362-59 PCT/US/DIV
Filing Date: March 1, 2004
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FIG. 1

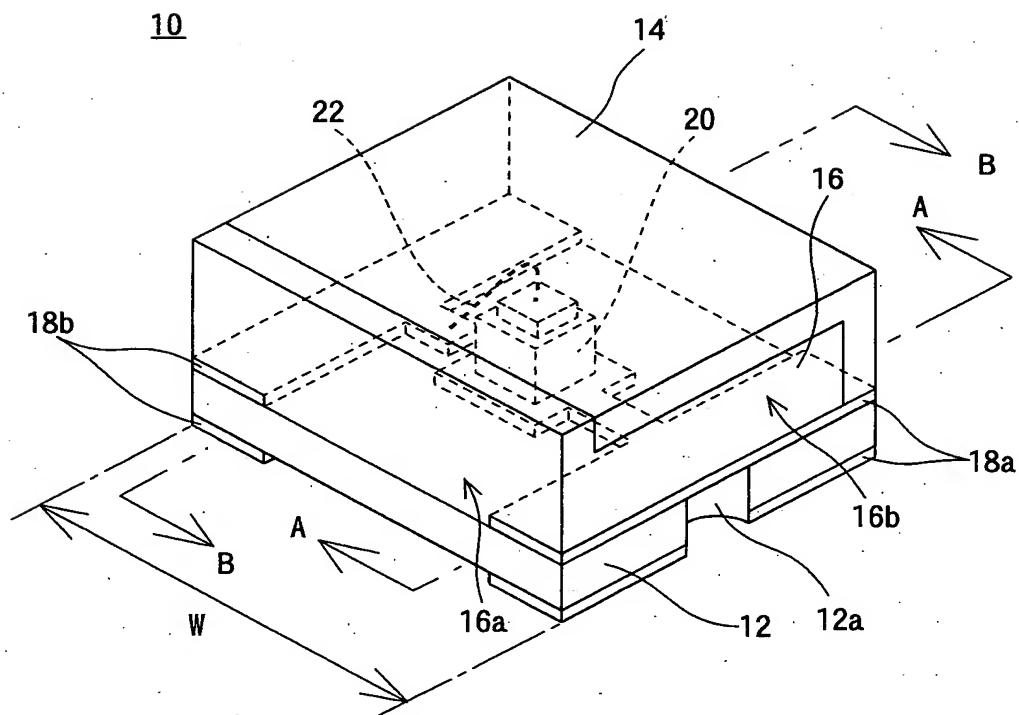


FIG. 2(A)

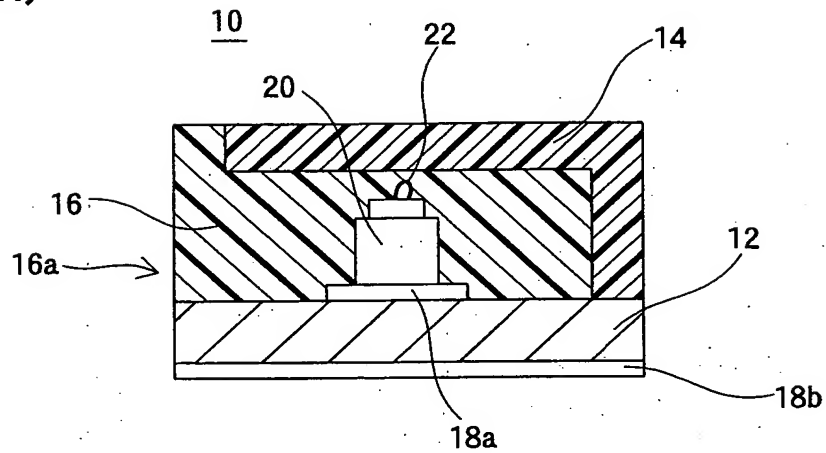


FIG. 2(B)

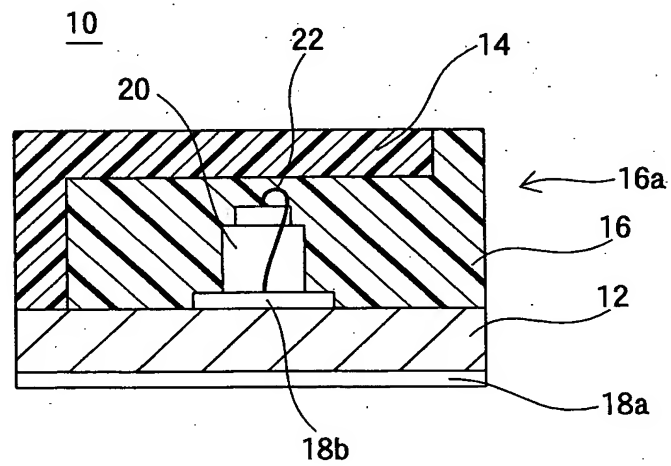


FIG. 3(A)

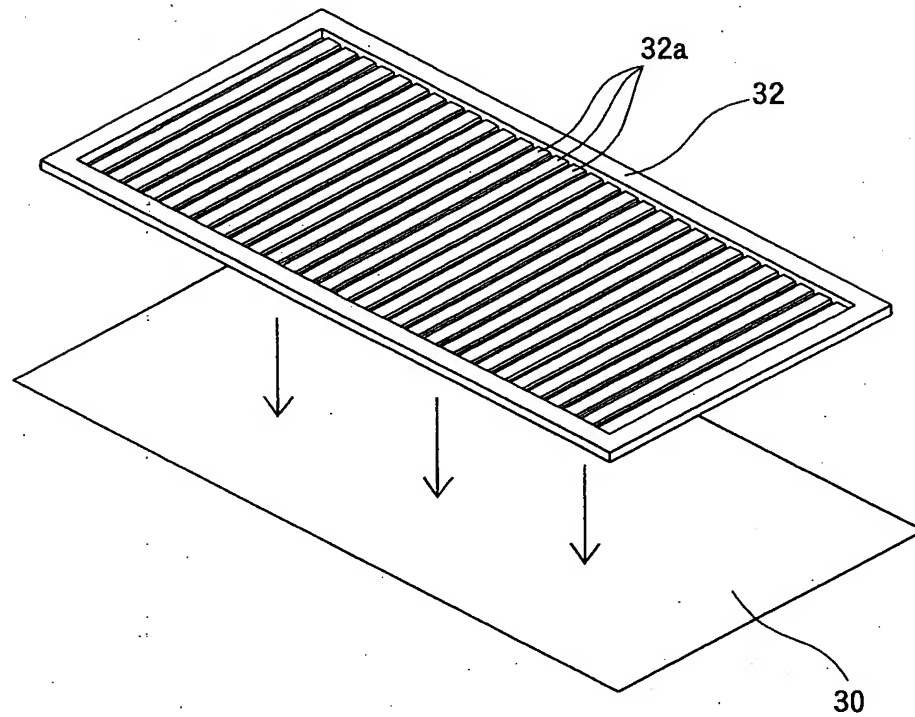


FIG. 3(B)

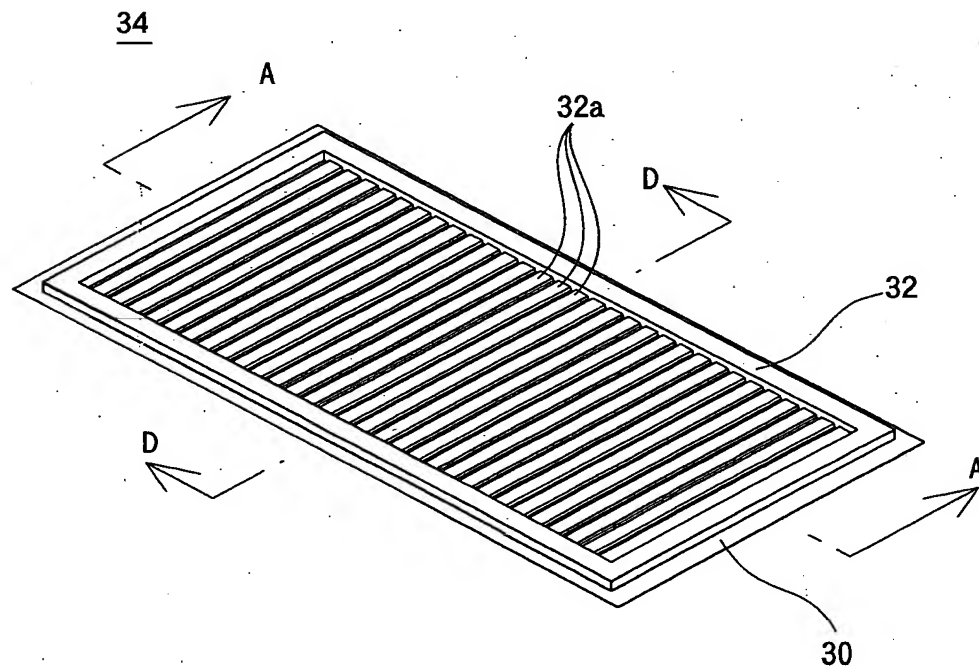


FIG. 4(A)

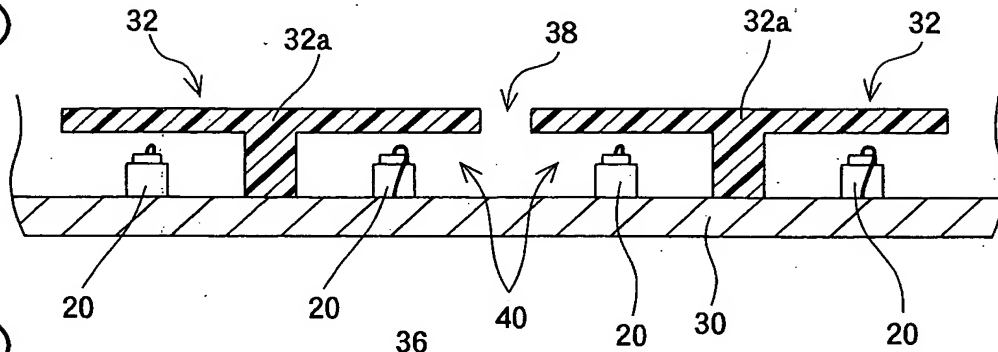


FIG. 4(B)

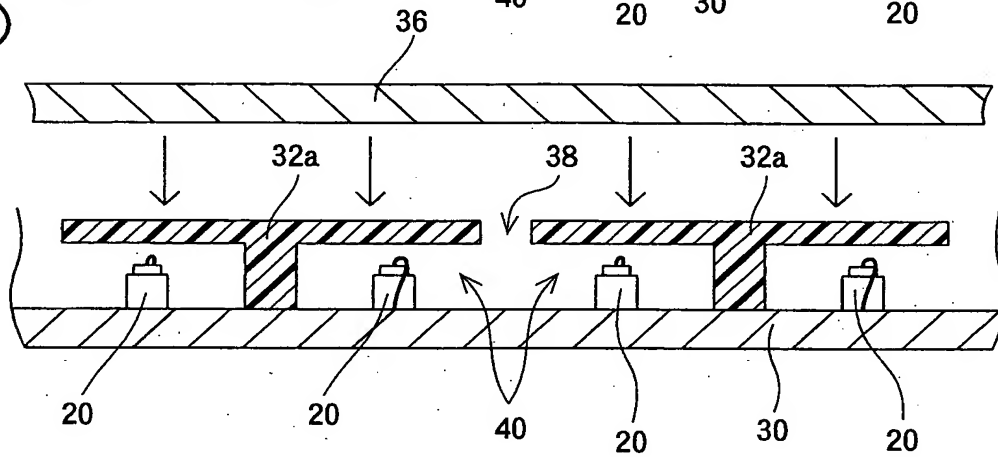


FIG. 4(C)

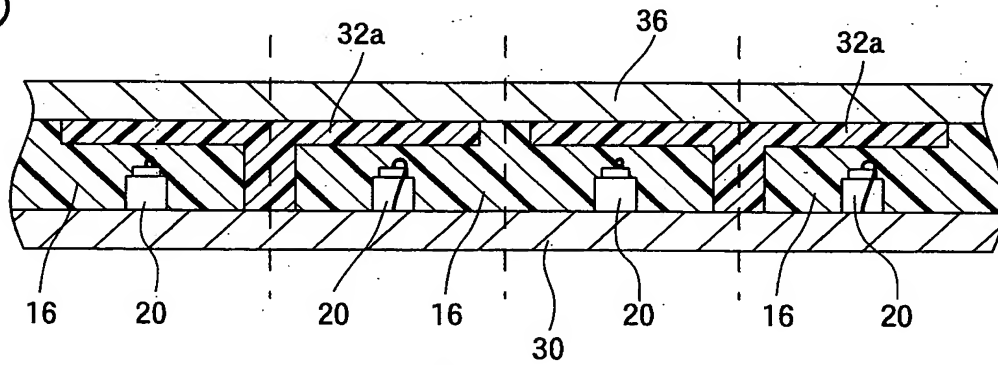


FIG. 4(D)

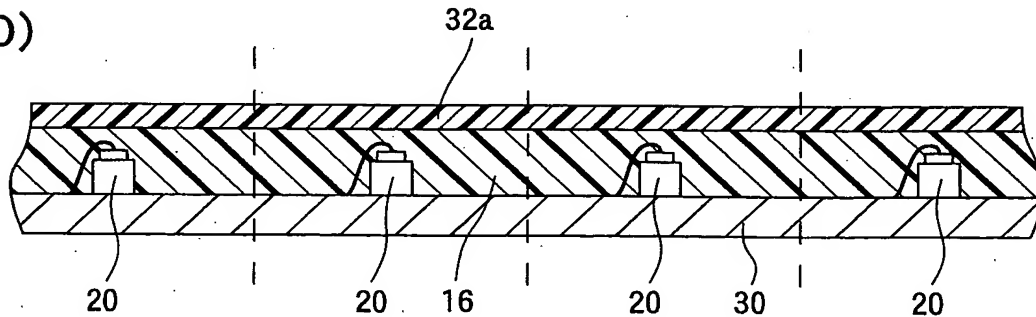


FIG. 5

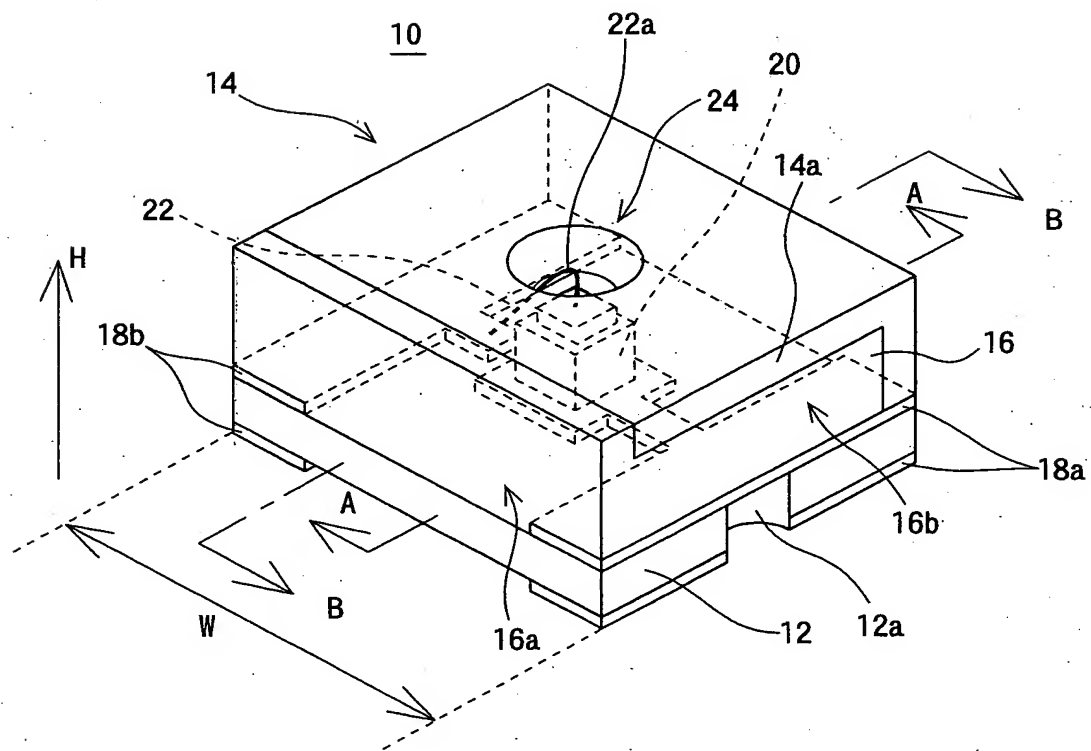


FIG. 6(A)

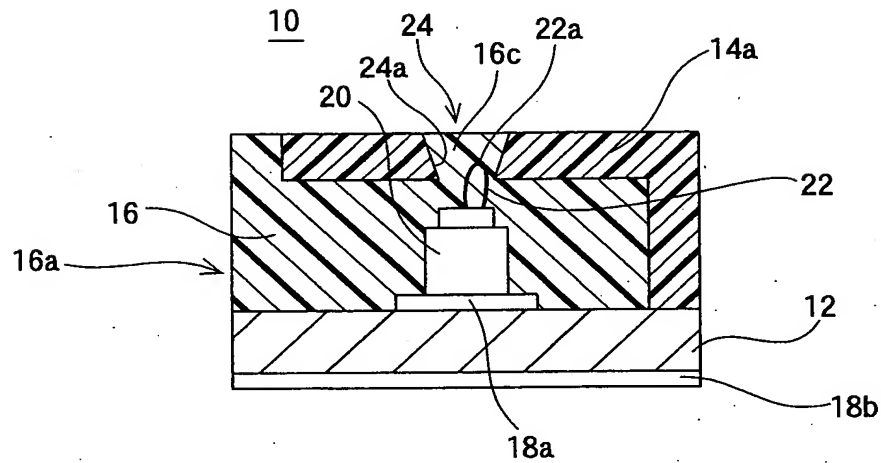


FIG. 6(B)

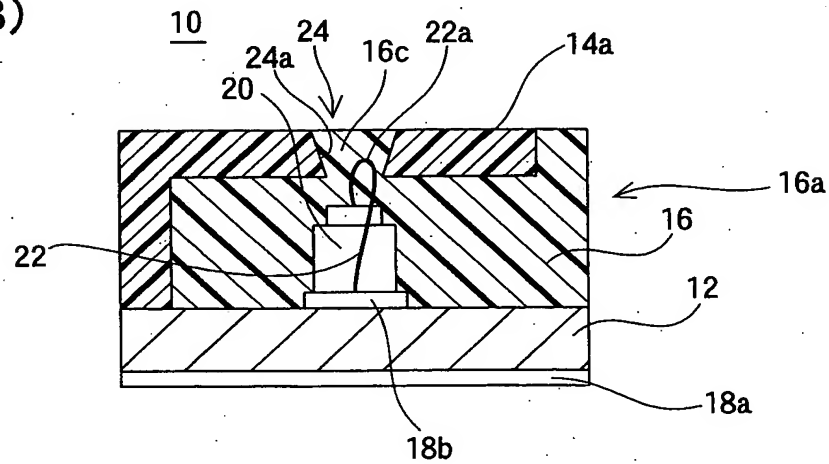


FIG. 7(A)

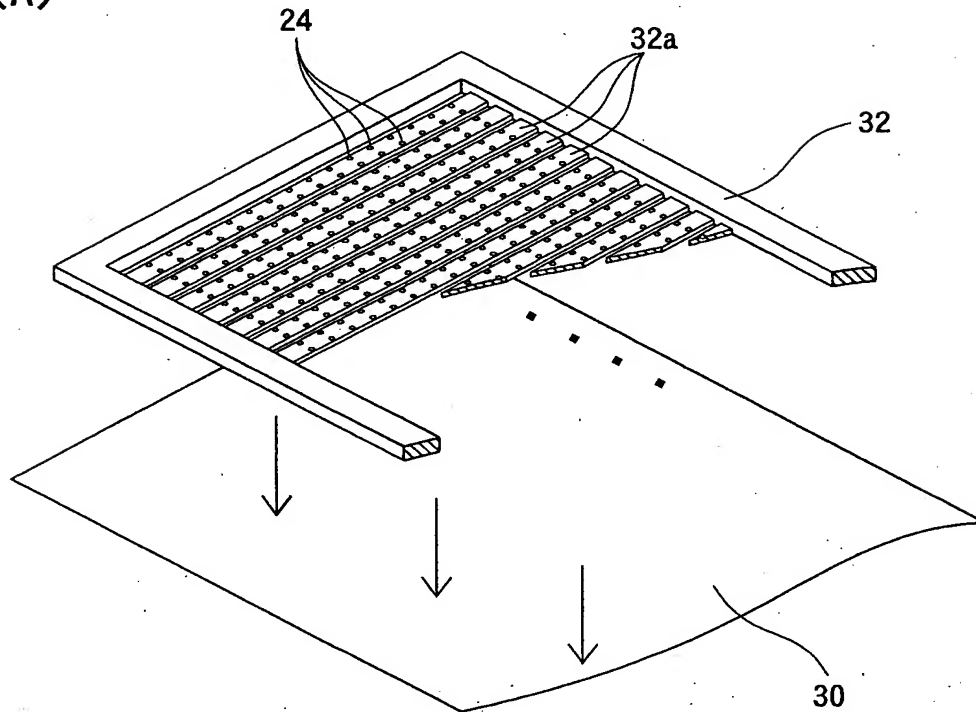


FIG. 7(B)

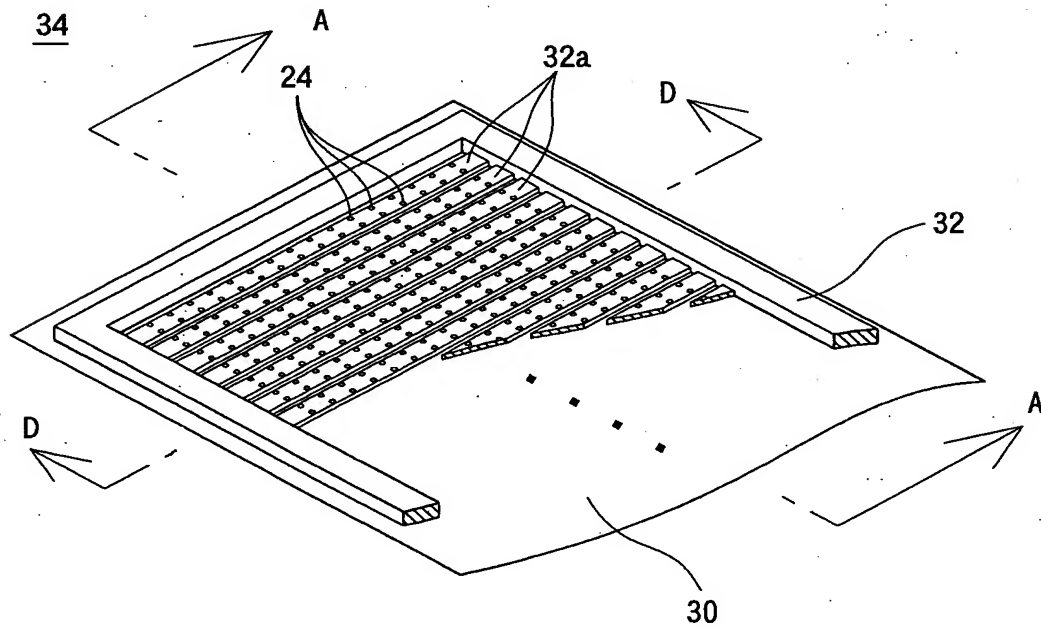


FIG. 8(A)

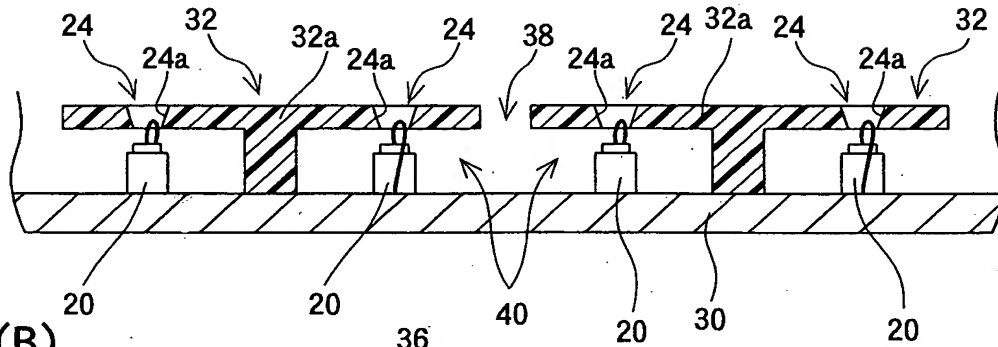


FIG. 8(B)

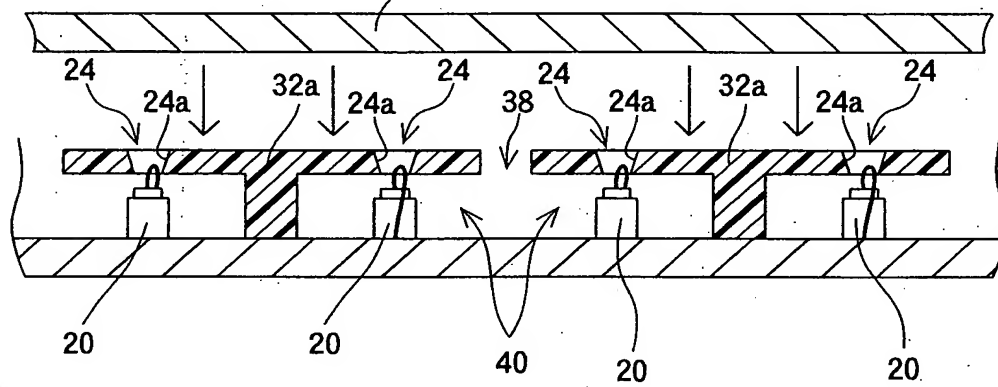


FIG. 8(C)

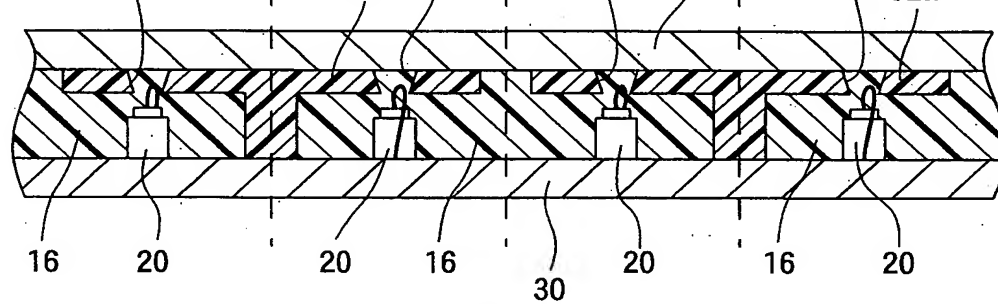


FIG. 8(D)

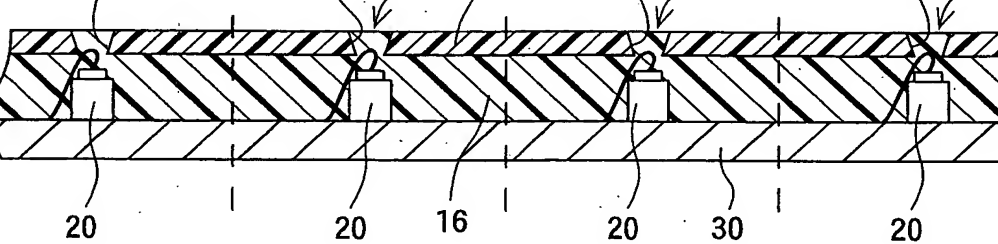


FIG. 9

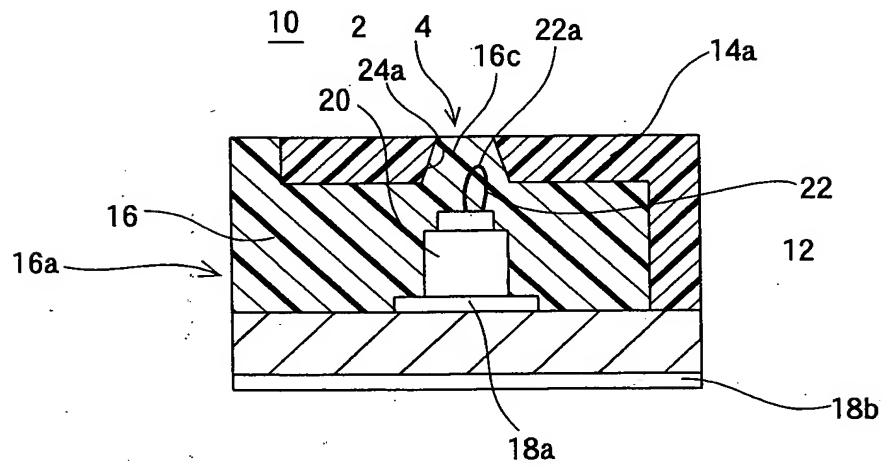


FIG. 10

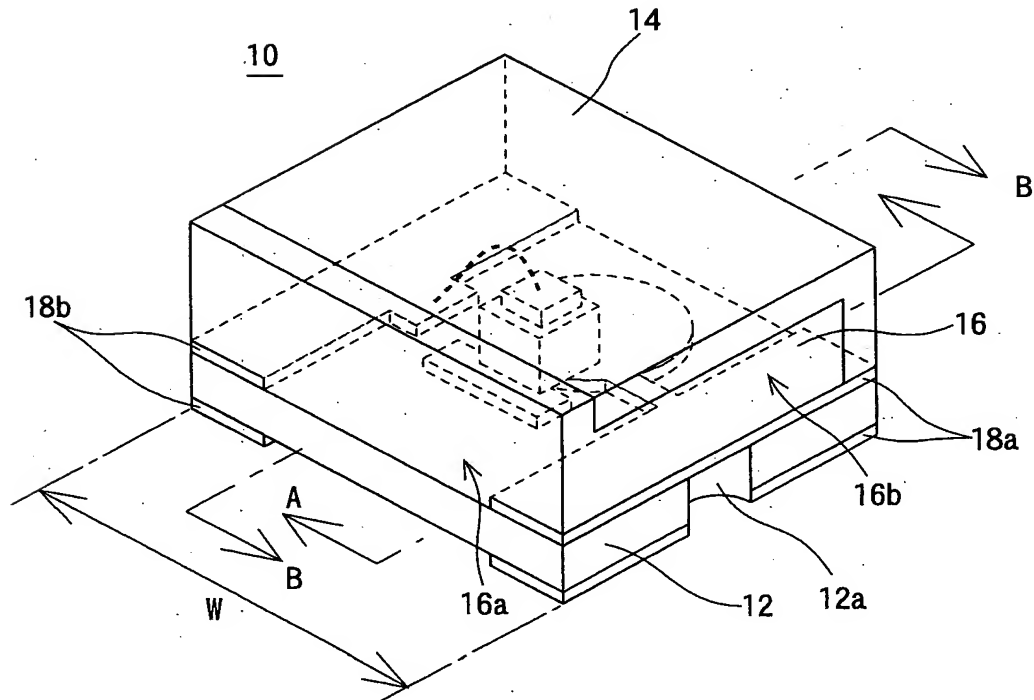


FIG. 11(A)

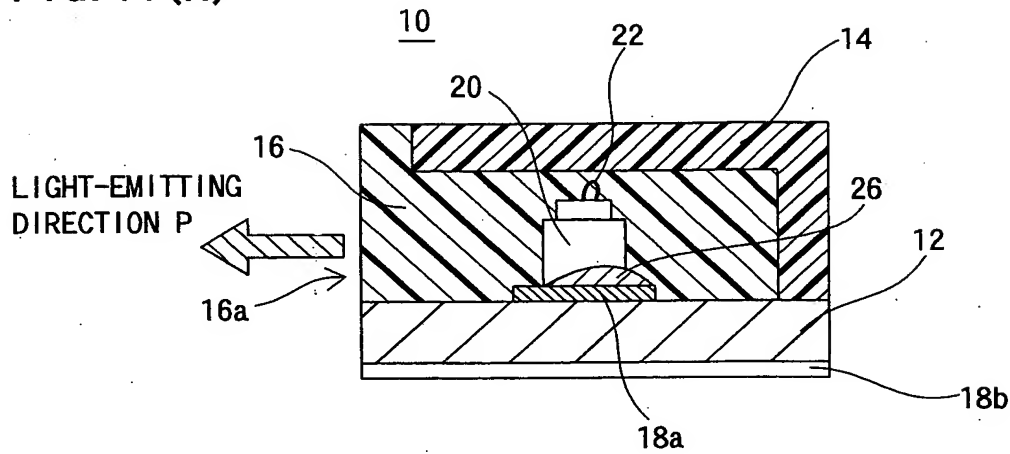


FIG. 11(B)

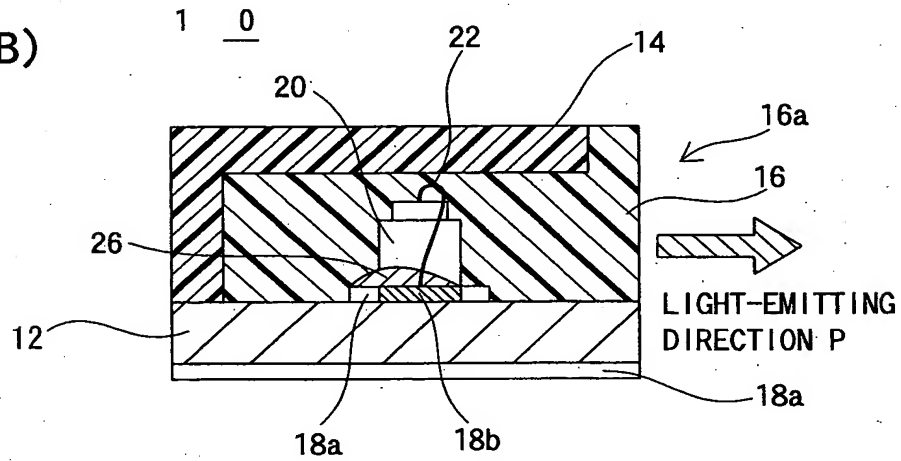


FIG. 12

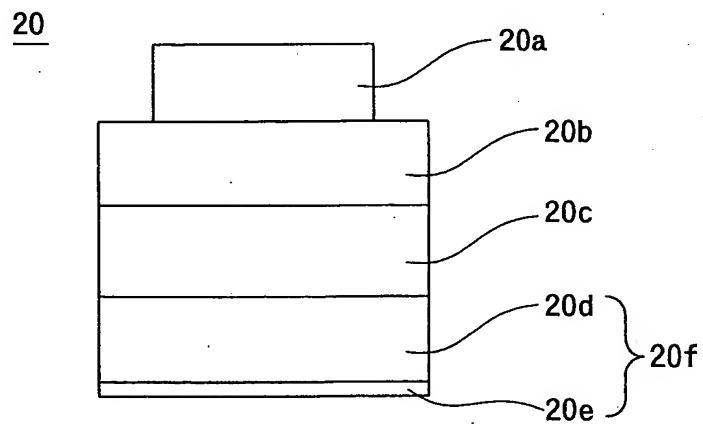


FIG. 13(A)

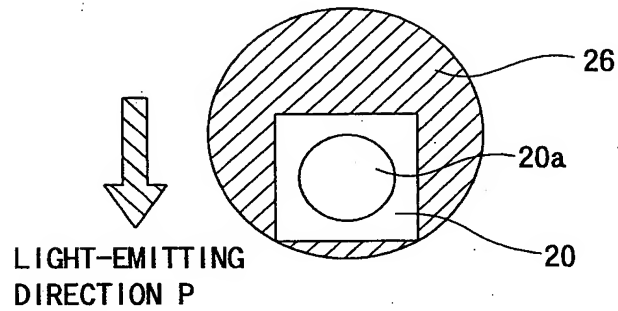


FIG. 13(B)

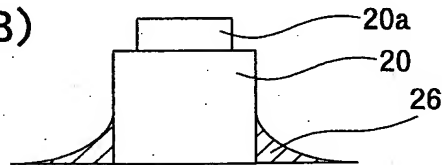


FIG. 13(C)

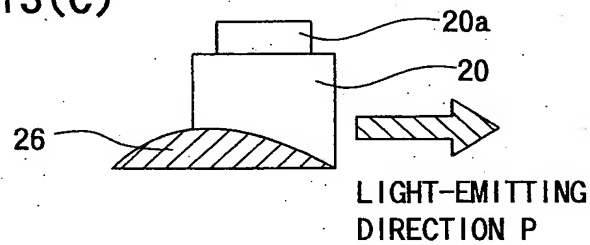


FIG. 13(D)

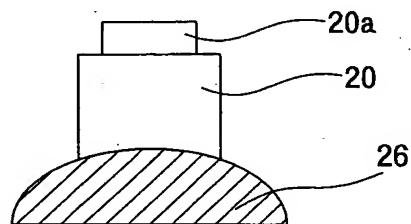


FIG. 14(A)

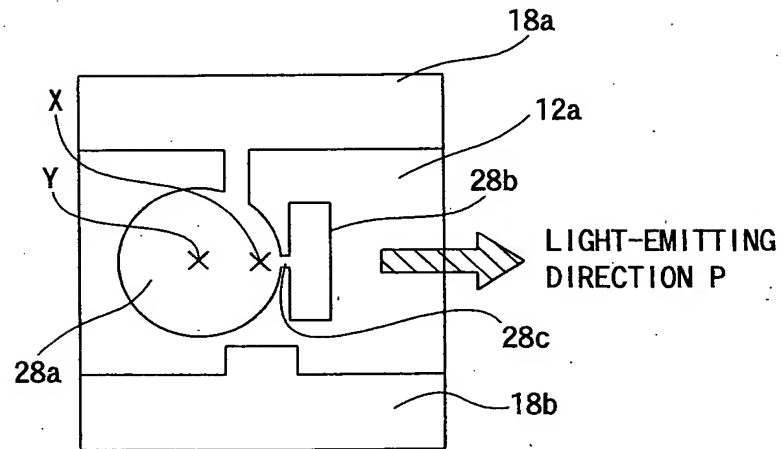


FIG. 14(B)

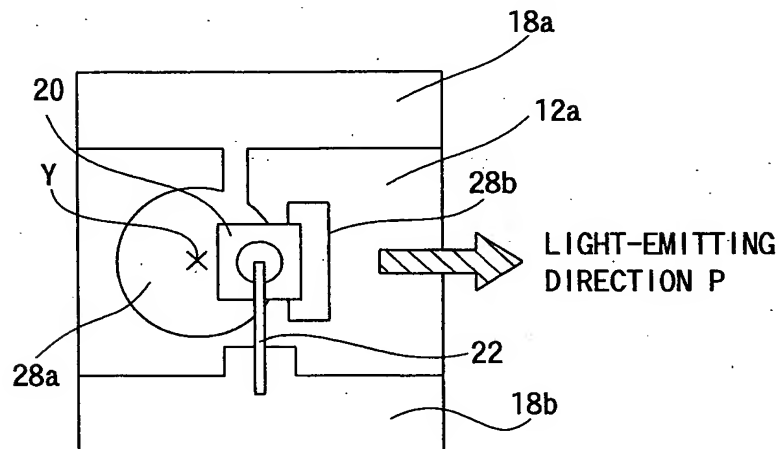


FIG. 15(A)

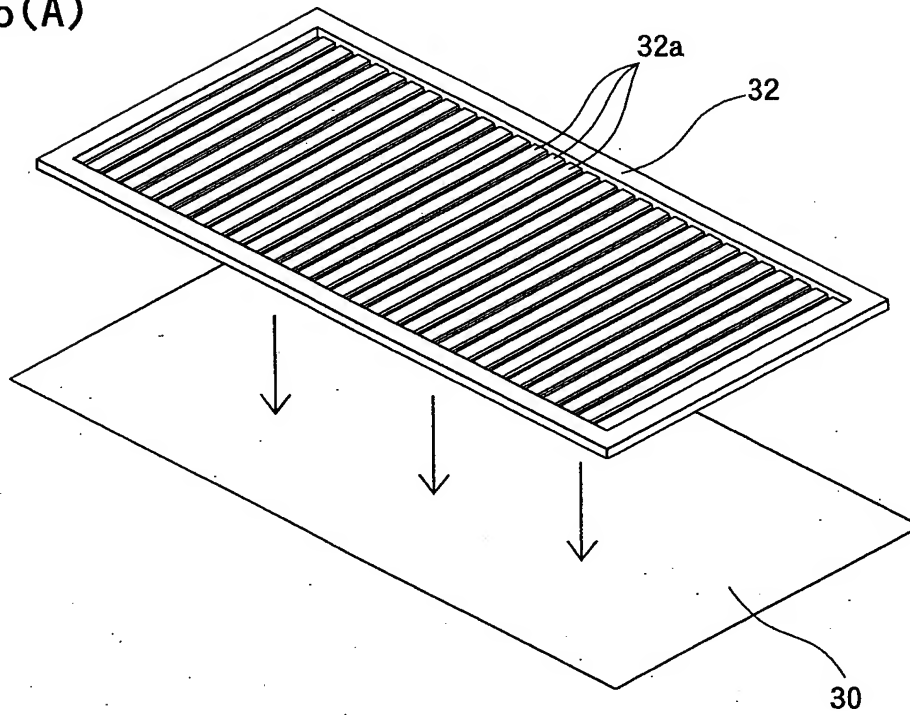
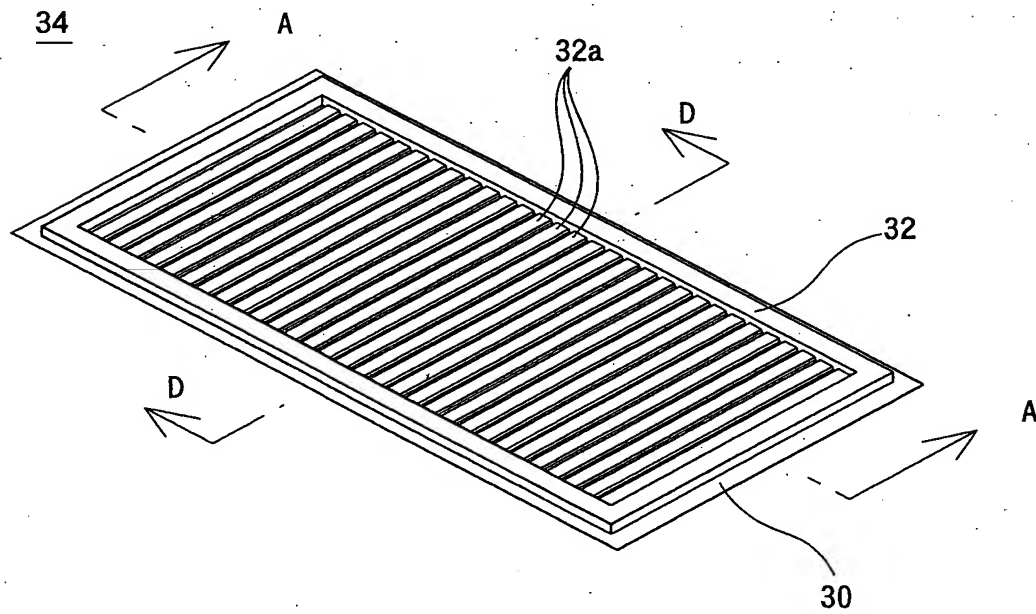


FIG. 15(B)



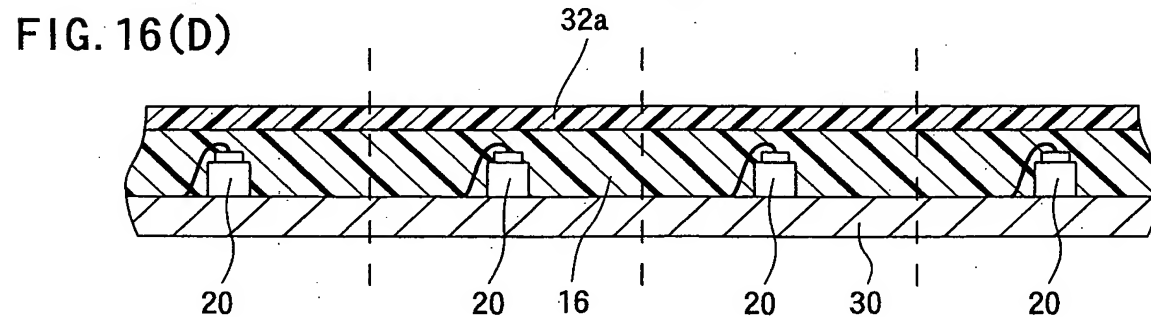
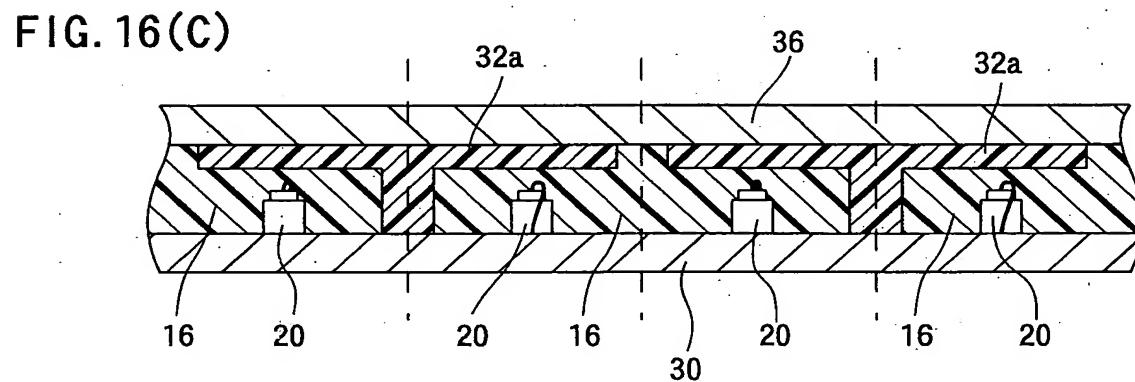
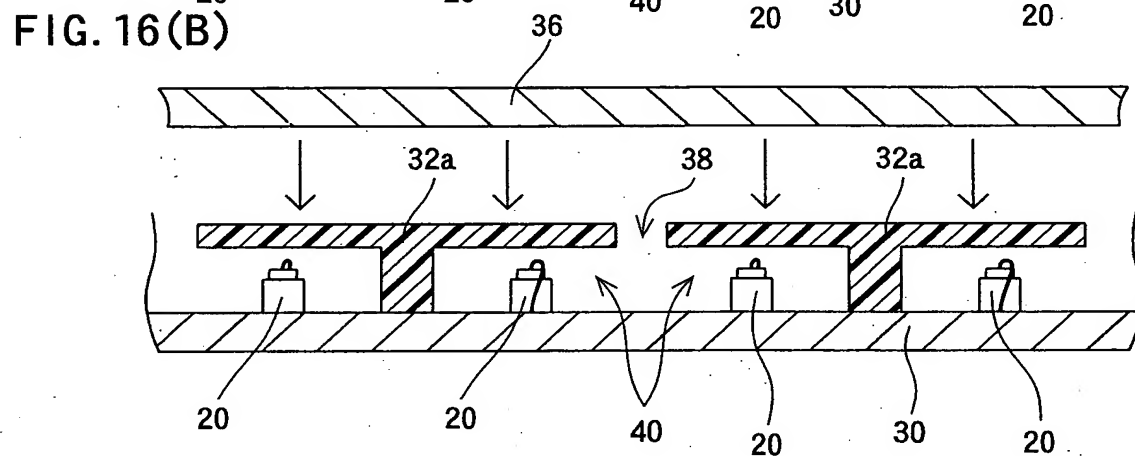
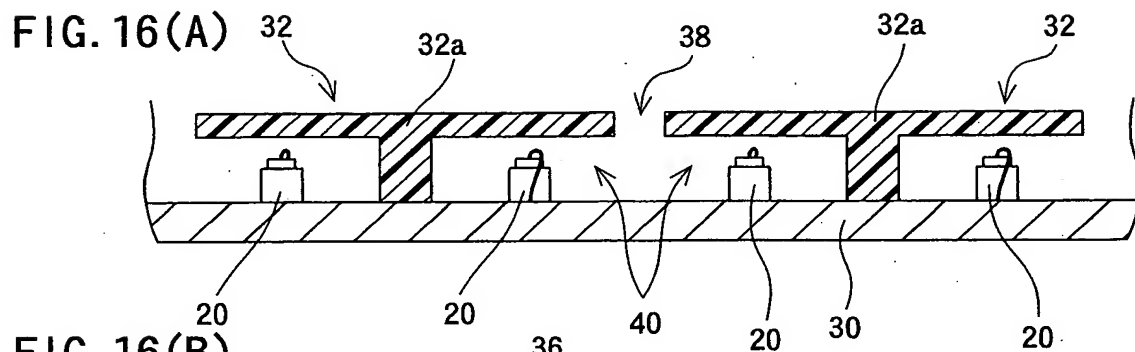


Figure 41 is a cross-sectional view of a semiconductor device. It shows a substrate 42 with a top layer 43. A central structure 44 is formed on the substrate, with a top layer 45. A curved layer 46 is shown on the right side of the device. The substrate 42 is divided into two regions, 42a and 42b, by a vertical line. The top layer 43 is also divided into two regions, 43a and 43b, by a vertical line. The central structure 44 is located on the 43a region. The curved layer 46 is located on the 43b region.

FIG. 19(A)

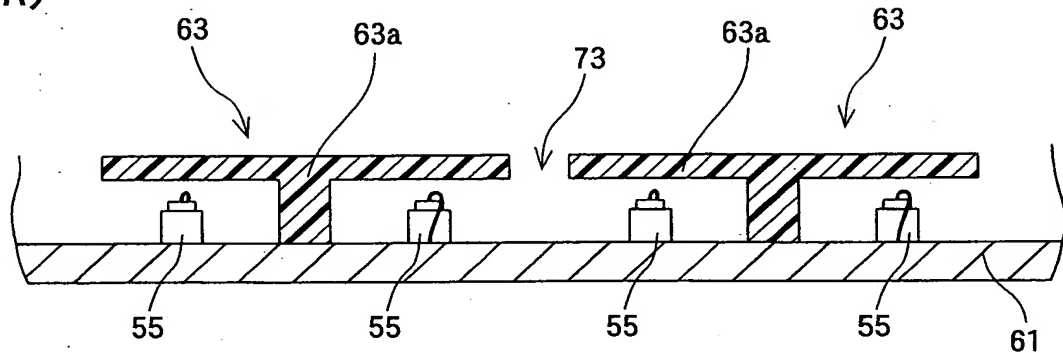


FIG. 19(B)

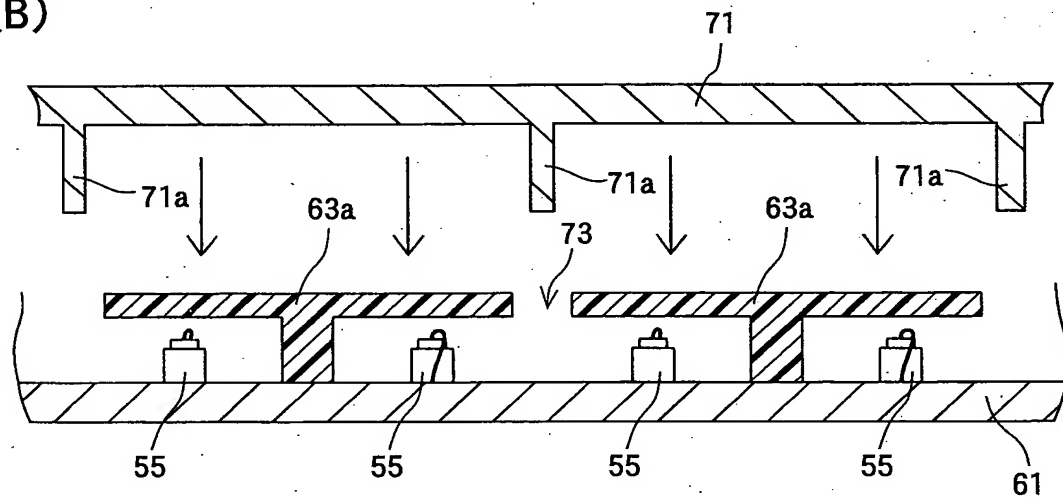


FIG. 19(C)

